

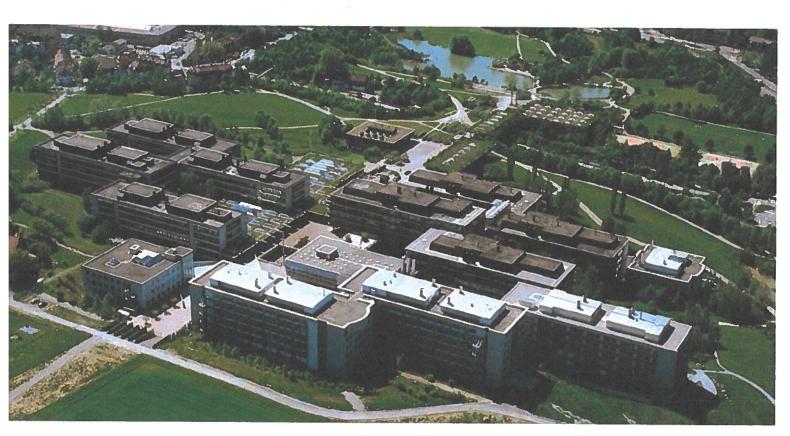


## Gemeinsame Jahrestagung in Zürich 26. - 30. August 2019

Universität Zürich, Irchel Campus

Réunion annuelle commune à Zürich 26 - 30 août 2019

## Programmübersicht Aperçu du programme



in Zusammenarbeit mit - en collaboration avec









				Aprization .	
				Van der Waals magnetic materials: growth and characterization	
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	1	IN	Novel properties and exciting perspectives are offered by two-dimensional magnetic materials, like binary MX <sub>2</sub> and ternary MYZ <sub>3</sub> (M is a metal element; X is a halogen; Y = Si, Ge or P, Z is a like binary MX <sub>2</sub> and ternary mYZ <sub>3</sub> (M is a metal element; X is a halogen; Y = Si, Ge or P, Z is a like binary MX <sub>2</sub> and ternary mYZ <sub>3</sub> (M is a metal element; X is a halogen; Y = Si, Ge or P, Z is a like binary MX <sub>2</sub> and ternary mYZ <sub>3</sub> (M is a metal element; X is a halogen; Y = Si, Ge or P, Z is a like binary MX <sub>2</sub> and ternary mYZ <sub>3</sub> (M is a metal element; X is a halogen; Y = Si, Ge or P, Z is a like binary MX <sub>2</sub> and ternary mYZ <sub>3</sub> (M is a metal element; X is a halogen; Y = Si, Ge or P, Z is a like binary mX <sub>2</sub> and ternary mYZ <sub>3</sub> (M is a metal element; X is a halogen; Y = Si, Ge or P, Z is a like binary mX <sub>2</sub> and ternary mYZ <sub>3</sub> (M is a metal element; X is a halogen; Y = Si, Ge or P, Z is a like binary mX <sub>2</sub> and ternary mYZ <sub>3</sub> (M is a metal element; X is a halogen; Y = Si, Ge or P, Z is a like binary mX <sub>2</sub> and ternary mYZ <sub>3</sub> (M is a metal element; X is a halogen; Y = Si, Ge or P, Z is a like binary mX <sub>2</sub> and ternary mYZ <sub>3</sub> (M is a metal element; X is a halogen; Y = Si, Ge or P, Z is a like binary mX <sub>2</sub> and ternary mYZ <sub>3</sub> (M is a metal element; X is a halogen; Y = Si, Ge or P, Z is a like binary mX <sub>2</sub> and ternary mX		
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L	+		_	Three Dimensional and Androach	
1 18	:00	125	اذ	Fadio ! Andreas Reyer	
1		1	1	Gilles Bourret ', Fedja Wendisch ', Michael Saller ', Alex Eduie ', Diwald ' Gilles Bourret ', Fedja Wendisch ', Michael Saller ', Alex Eduie ', Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Maurizio Musso ', Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Oliver Diwald ' Marcel Rey <sup>2</sup> , Nicolas Vogel <sup>2</sup> , Nicolas V	
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	1		1	ing focused ion beam (FIB)-Inipations in focused ion beam (FIB)-Inipations in growth. In this work, we have further investigated the possibility of single InGaAs quality of North in the shell. The nanowires show good emission, proving the high material quality of North in the shell. The nanowires show good emission, proving the high material quality of North in the shell. The nanowires show good emission, proving the high implantation. By comparison with randomly nucleated NWs, we find some C-dop with FIB-implantation. By comparison process.	
	1		1	wires using this technique, via the ground emission, proving the highested NWs, we find some U-do	
	1		1	walls in the shell. The nanowires should with randomly nucleurs	
	1		1	growth. In this work, we have tuttor growth of GaAs nanowires containing the high material quality of New wires using this technique, via the growth of GaAs nanowires the high material quality of New wells in the shell. The nanowires show good emission, proving the high material quality of New wells in the shell. The nanowires show good emission, proving the high material quality of New yellow with randomly nucleated NWs, we find some C-dop grown via FIB-implantation. By comparison with randomly nucleated NWs, we find some C-dop grown via FIB-implantation. By comparison with randomly nucleated NWs, we find some C-dop grown via FIB-implantation. By comparison with randomly nucleated NWs, we find some C-dop grown via FIB-implantation.	
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